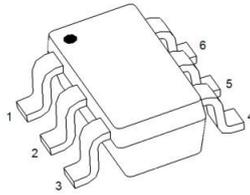
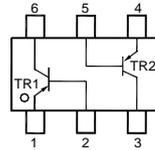


DUAL TRANSISTOR (PNP+PNP)

SOT-363

MARKING: K4M
MAXIMUM RATINGS ($T_a=25^{\circ}\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Collector Base Voltage	$-V_{\text{CBO}}$	160	V
Collector Emitter Voltage	$-V_{\text{CEO}}$	150	V
Emitter Base Voltage	$-V_{\text{EBO}}$	5	V
Collector Current Continuous	$-I_{\text{C}}$	600	mA
Power Dissipation	P_{tot}	200	mW
Junction Temperature	T_{j}	150	$^{\circ}\text{C}$
Storage Temperature Range	T_{stg}	- 55 to + 150	$^{\circ}\text{C}$

ELECTRICAL CHARACTERISTICS ($T_a=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Min.	Max.	Unit
DC Current Gain				
at $-V_{\text{CE}} = 5\text{ V}$, $-I_{\text{C}} = 1\text{ mA}$	h_{FE}	50	-	-
at $-V_{\text{CE}} = 5\text{ V}$, $-I_{\text{C}} = 10\text{ mA}$	h_{FE}	60	240	-
at $-V_{\text{CE}} = 5\text{ V}$, $-I_{\text{C}} = 50\text{ mA}$	h_{FE}	50	-	-
Collector Base Cutoff Current				
at $-V_{\text{CB}} = 120\text{ V}$	$-I_{\text{CBO}}$	-	50	nA
Emitter Base Cutoff Current				
at $-V_{\text{EB}} = 3\text{ V}$	$-I_{\text{EBO}}$	-	50	nA
Collector Base Breakdown Voltage				
at $-I_{\text{C}} = 100\text{ }\mu\text{A}$	$-V_{(\text{BR})\text{CBO}}$	160	-	V
Collector Emitter Breakdown Voltage				
at $-I_{\text{C}} = 1\text{ mA}$	$-V_{(\text{BR})\text{CEO}}$	150	-	V
Emitter Base Breakdown Voltage				
at $-I_{\text{E}} = 10\text{ }\mu\text{A}$	$-V_{(\text{BR})\text{EBO}}$	5	-	V
Collector Emitter Saturation Voltage				
at $-I_{\text{C}} = 10\text{ mA}$, $-I_{\text{B}} = 1\text{ mA}$	$-V_{\text{CE}(\text{sat})}$	-	0.2	V
at $-I_{\text{C}} = 50\text{ mA}$, $-I_{\text{B}} = 5\text{ mA}$	$-V_{\text{CE}(\text{sat})}$	-	0.5	V
Base Emitter Saturation Voltage				
at $-I_{\text{C}} = 10\text{ mA}$, $-I_{\text{B}} = 1\text{ mA}$	$-V_{\text{BE}(\text{sat})}$	-	1	V
at $-I_{\text{C}} = 50\text{ mA}$, $-I_{\text{B}} = 5\text{ mA}$	$-V_{\text{BE}(\text{sat})}$	-	1	V
Gain Bandwidth Product				
at $-V_{\text{CE}} = 10\text{ V}$, $-I_{\text{C}} = 10\text{ mA}$, $f = 100\text{ MHz}$	f_{T}	100	300	MHz
Output Capacitance				
at $-V_{\text{CB}} = 10\text{ V}$, $f = 1\text{ MHz}$	C_{obo}	-	6	pF

Typical Characteristics

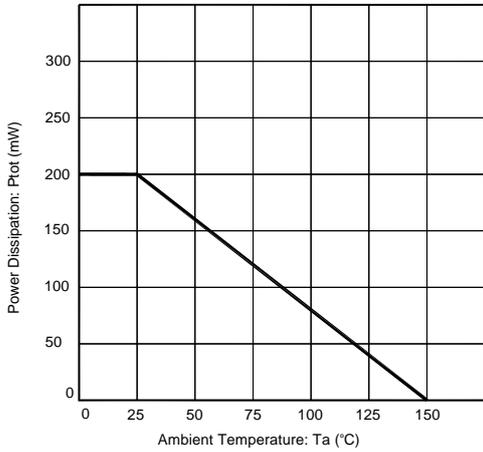


Fig. 1 Max Power Dissipation vs Ambient Temperature

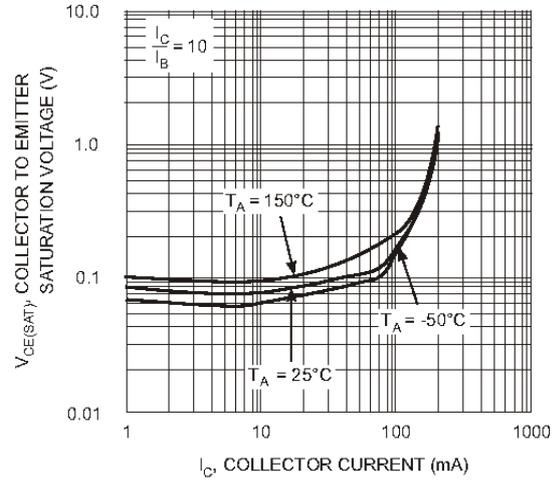


Fig. 2, Collector Emitter Saturation Voltage vs. Collector Current

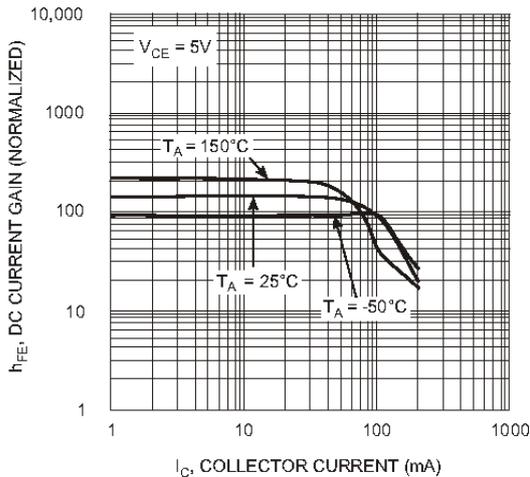


Fig. 3, DC Current Gain vs. Collector Current

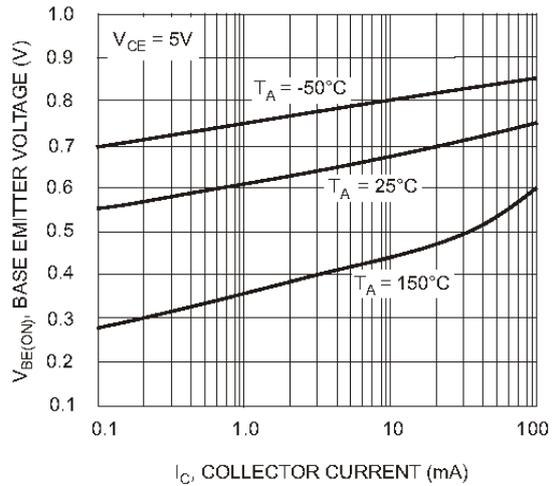


Fig. 4, Base Emitter Voltage vs. Collector Current

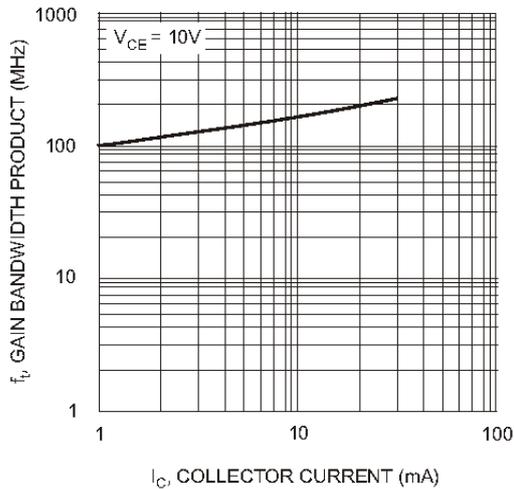
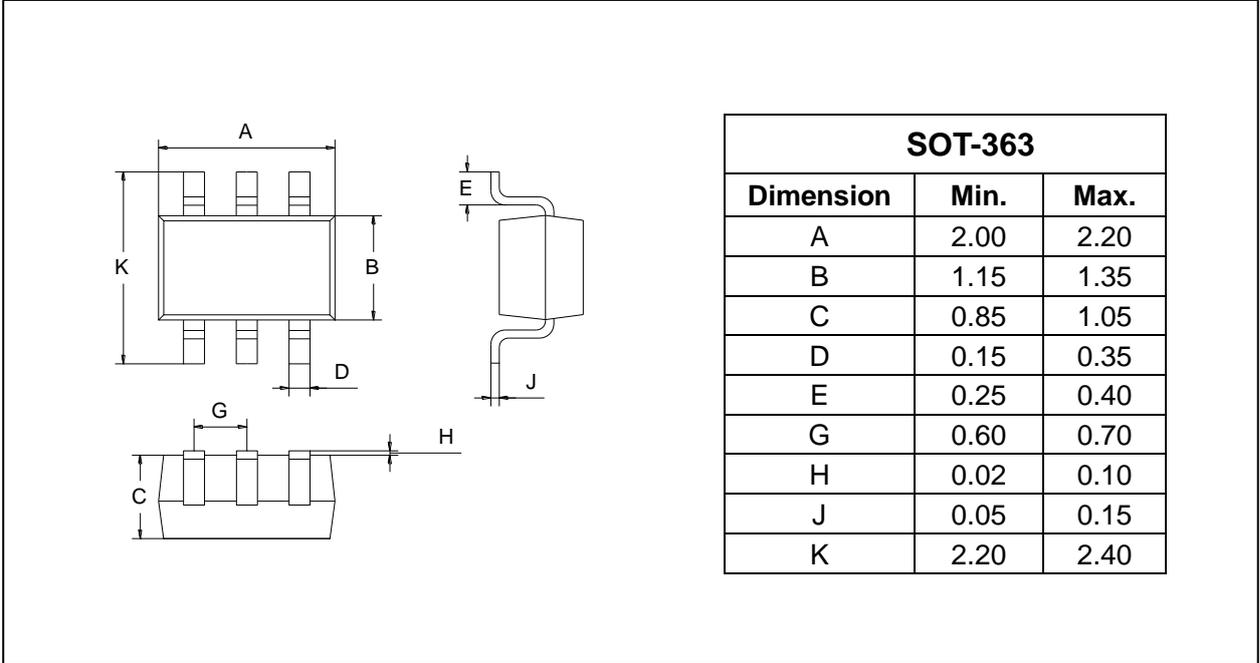


Fig. 5, Gain Bandwidth Product vs Collector Current

Plastic surface mounted package

SOT-363



SOLDERING FOOTPRINT

